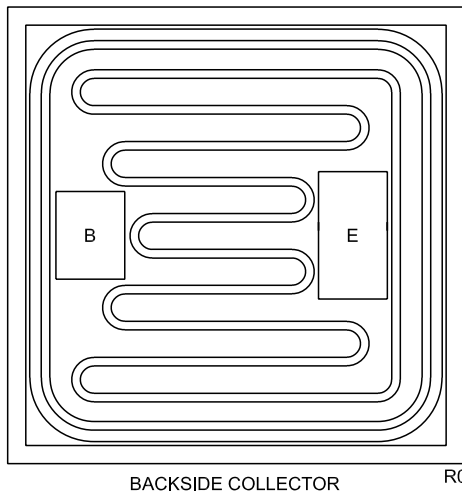


**PROCESS DETAILS**

Process	Epitaxial Planar
Die Size	31.5 x 31.5 MILS
Die Thickness	7.1 MILS
Base Bonding Pad Area	4.7 x 6.7 MILS
Emitter Bonding Pad Area	4.7 x 8.7 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

**GEOMETRY**



**GROSS DIE PER 4 INCH WAFER**

11,210

**PRINCIPAL DEVICE TYPES**

CMPT404A  
MPS404A

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R0 (5- January 2006)